



MMBTSA1365

PNP Silicon Epitaxial Planar Transistor

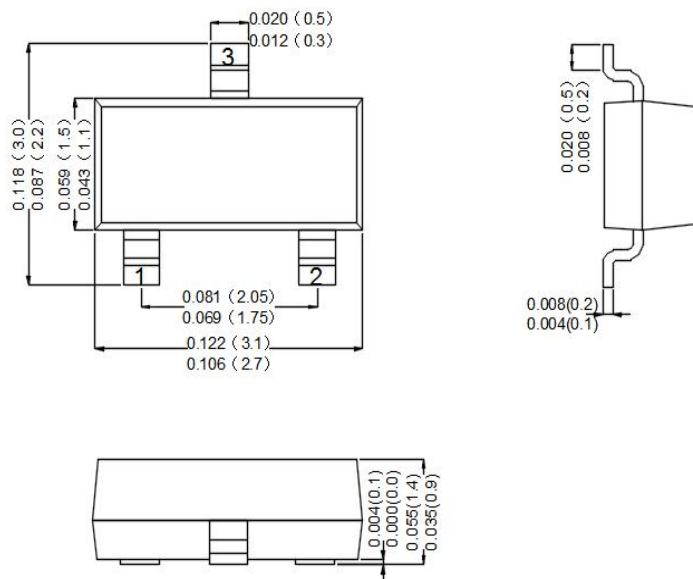
Features

- For high current drive application
- The transistor is subdivided into three groups E, F and G according to its DC current gain.

SOT-23

Mechanical Data

- Case: Molded Plastic, SOT-23
- Epoxy: UL 94V-0 rate flame retardant
- Terminals: Plated Leads Solderable per MIL-STD-750, Method-2026.
- Marking: marked on body
- Mounting Position : Any.
- Equivalent Circuit:



Dimensions in inches and (millimeters)

Maximum Ratings Maximum Ratings (Rating at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	25	V
Collector Emitter Voltage	$-V_{CEO}$	20	V
Emitter Base Voltage	$-V_{EBO}$	4	V
Collector Current	$-I_C$	700	mA
Peak Collector Current	$-I_{CM}$	1	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_s	- 55 to + 150	°C



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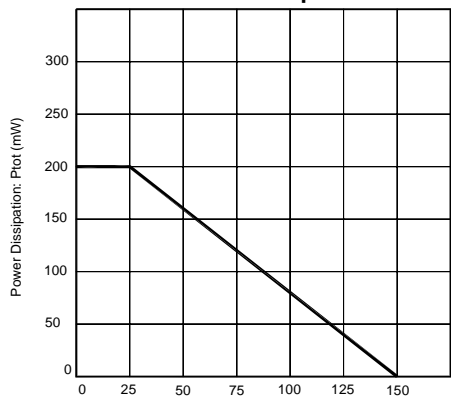
Electrical Characteristics (Rating at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 4\text{ V}$, $-I_C = 100\text{ mA}$	E	h_{FE}	150	-	300	-
	F	h_{FE}	250	-	500	-
	G	h_{FE}	400	-	800	-
Collector Cutoff Current at $-V_{CB} = 25\text{ V}$	$-I_{CBO}$	-	-	1	μA	
Emitter Cutoff Current at $-V_{EB} = 2\text{ V}$	$-I_{EBO}$	-	-	1	μA	
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	25	-	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CEO}$	20	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	4	-	-	V	
Collector Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 25\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V	
Transition Frequency at $-V_{CE} = 6\text{ V}$, $I_E = 10\text{ mA}$	f_T	-	180	-	MHz	



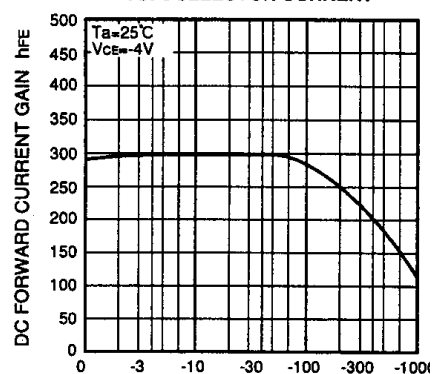
Rating And Characteristic Curves

Power Dissipation vs Ambient Temperature



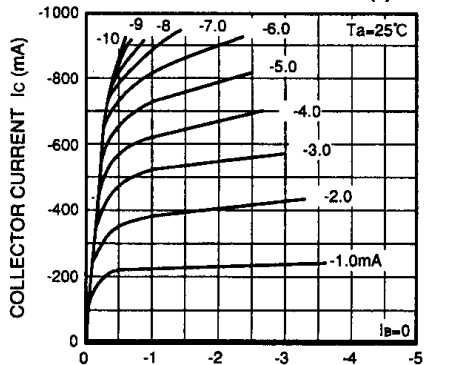
Ambient Temperature: T_a (°C)

DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT



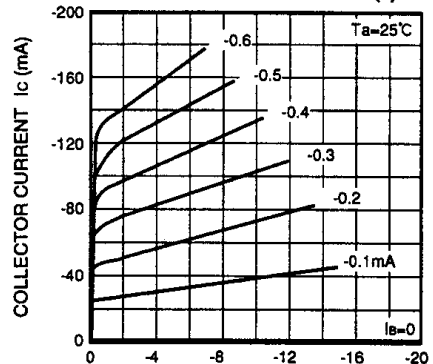
COLLECTOR CURRENT I_c (mA)

COMMON EMITTER OUTPUT (1)



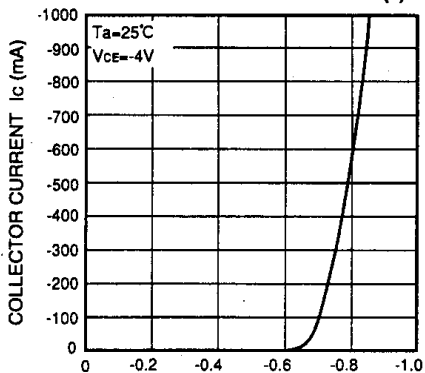
COLLECTOR TO EMITTER VOLTAGE V_{CE} (V)

COMMON EMITTER OUTPUT (2)



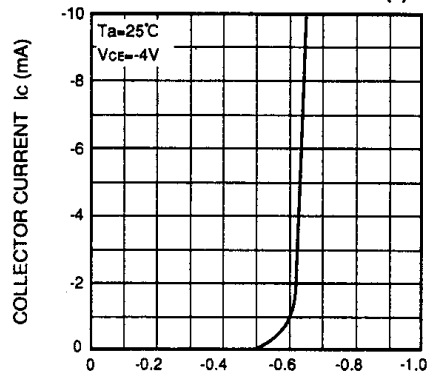
COLLECTOR TO EMITTER VOLTAGE V_{CE} (V)

COMMON EMITTER TRANSFER (1)



BASE TO EMITTER VOLTAGE V_{BE} (V)

COMMON EMITTER TRANSFER(2)



BASE TO EMITTER VOLTAGE V_{BE} (V)



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